

Title (en)  
METHOD FOR PRODUCING NANOSTRUCTURES

Title (de)  
VERFAHREN ZUR HERSTELLUNG VON NANOSTRUKTUREN

Title (fr)  
PROCEDE DE FABRICATION DE NANOSTRUCTURES

Publication  
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Application  
**EP 16729826 A 20160603**

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Abstract (en)  
[origin: WO2016198341A1] The invention relates to a method for producing at least one type of nanostructure (30, 35, 37), including the following steps: partially covering a surface of a layer or a single-crystal multilayer structure (3) using a discontinuous mask (4) which forms discrete islands having at least one sub-micrometric side dimension and is made of a material having an evaporation temperature greater than that of said layer or multilayer structure; and vacuum heating said layer or multilayer structure to a so-called etching temperature which is greater than the evaporation temperature of said layer or multilayer structure but less than that of said mask, so as to cause said layer or multilayer structure to evaporate outside the regions covered by said mask. The invention further relates to structures that can be produced using a method of this type.

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